

## PMG85XP

# 20 V, 2 A P-channel Trench MOSFET Rev. 1 — 28 June 2011

Product data sheet

#### 1. **Product profile**

#### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

Low threshold voltage

Trench MOSFET technology

Very fast switching

#### 1.3 Applications

Relay driver

High-speed line driver

High-side loadswitch

Switching circuits

#### 1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
$V_{GS}$	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_j = 25 \text{ °C}$	<u>[1]</u>	-	-	-2	Α
Static charact	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2 \text{ A}; T_j = 25 \text{ °C}$		-	90	115	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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## 2. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	П. П. П.	D
2	D	drain	6 5 4	
3	G	gate		
4	S	source	0	
5	D	drain	□1 □2 □3	Ś
6	D	drain	SOT363 (TSSOP6)	017aaa094

## 3. Ordering information

#### Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMG85XP	TSSOP6	plastic surface-mounted package; 6 leads	SOT363		

## 4. Marking

#### Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PMG85XP	YA%

[1] % = placeholder for manufacturing site code

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_j = 25 \text{ °C}$	<u>[1]</u>	-	-2	Α
		$V_{GS} = -4.5 \text{ V}; T_j = 100 \text{ °C}$	<u>[1]</u>	-	-1.3	Α
I <sub>DM</sub>	peak drain current	$T_{amb} = 25  ^{\circ}C$ ; single pulse; $t_p \le 10  \mu s$		-	-8	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	375	mW
			[1]	-	725	mW
		T <sub>sp</sub> = 25 °C		-	2400	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	n diode					
Is	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	-0.7	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

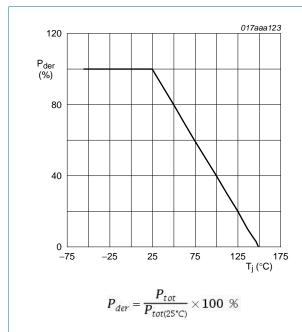


Fig 1. Normalized total power dissipation as a function of junction temperature

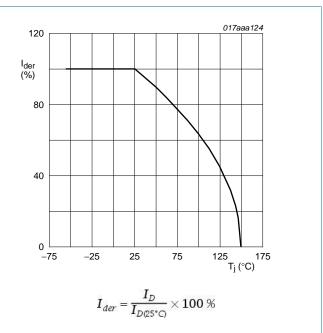
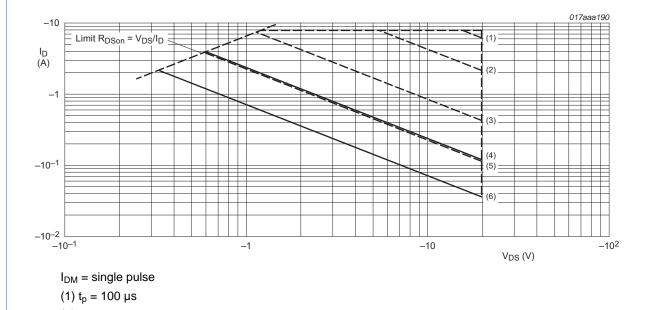


Fig 2. Normalized continuous drain current as a function of junction temperature

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- (2)  $t_p = 1 \text{ ms}$
- (3)  $t_p = 10 \text{ ms}$
- (4) DC;  $T_{sp} = 25$  °C
- $(5) t_p = 100 ms$
- (6) DC; T<sub>amb</sub> = 25 °C; drain mounting pad 6 cm<sup>2</sup>

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	290	334	K/W
			[2]	-	150	173	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	45	52	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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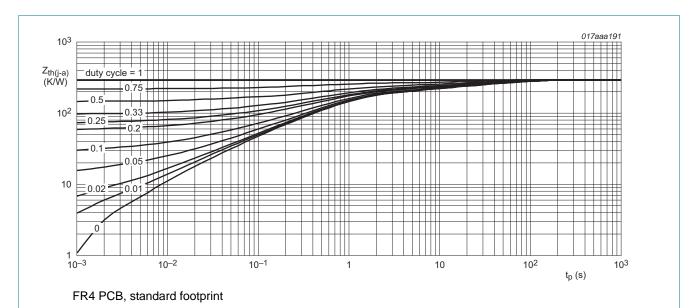


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

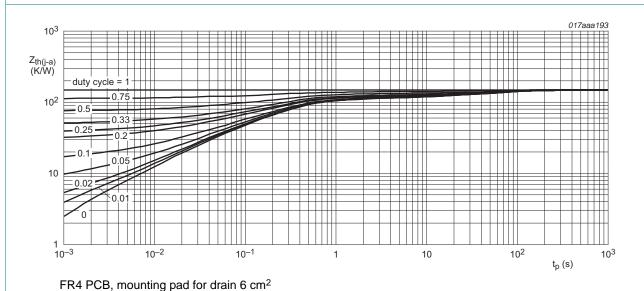


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 20 V, 2 A P-channel Trench MOSFET

## 7. Characteristics

#### Table 7. Characteristics

Table 1.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.65	-0.9	-1.15	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-15	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -2 \text{ A}; T_j = 25 \text{ °C}$	-	90	115	mΩ
resistance	resistance	$V_{GS}$ = -4.5 V; $I_{D}$ = -2 A; $T_{j}$ = 150 °C	-	130	166	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -2 \text{ A}; T_j = 25 \text{ °C}$	-	125	160	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = -5 \text{ V}; I_D = -2 \text{ A}; T_j = 25 \text{ °C}$	-	6.3	-	S
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -1 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	4.8	7.2	nC
$Q_GS$	gate-source charge	T <sub>j</sub> = 25 °C	-	1.1	-	nC
$Q_{GD}$	gate-drain charge		-	1	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = -10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	560	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	80	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	55	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $V_{GS}$ = -4.5 V; $R_{G(ext)}$ = 6 $\Omega$ ;	-	13	-	ns
t <sub>r</sub>	rise time	$T_j = 25 ^{\circ}\text{C};  I_D = -2.5 ^{\circ}\text{A}$	-	35	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	39	-	ns
t <sub>f</sub>	fall time		-	25	-	ns
Source-d	rain diode					
$V_{SD}$	source-drain voltage	$I_S = -0.7 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_i = 25 \text{ °C}$	-	-0.7	-1.2	V

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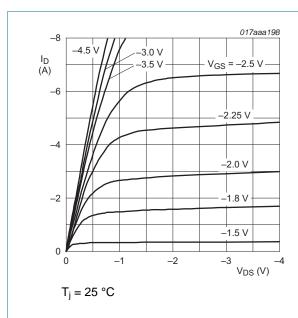
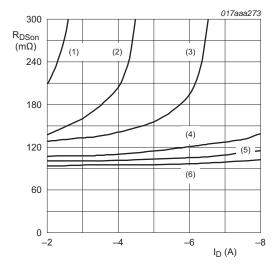


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C$ 

(1)  $V_{GS} = -2.0 \text{ V}$ 

(2)  $V_{GS} = -2.25 \text{ V}$ 

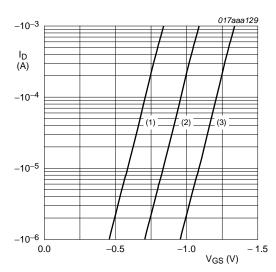
(3)  $V_{GS} = -2.5 \text{ V}$ 

(4)  $V_{GS} = -3.0 \text{ V}$ 

(5)  $V_{GS} = -3.5 \text{ V}$ 

(6)  $V_{GS} = -4.5 \text{ V}$ 

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



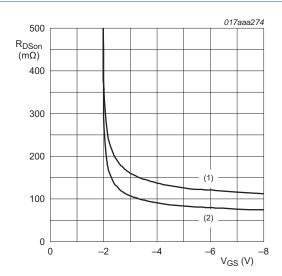
 $T_j = 25$  °C;  $V_{DS} = -3$  V

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $I_D = -2.5 A$ 

(1)  $T_i = 125 \, ^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

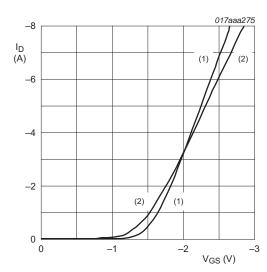
Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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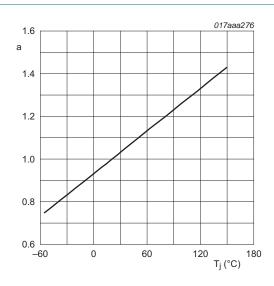


 $V_{DS} > I_D \times R_{DSon}$ 

(1) 
$$T_j = 25 \, ^{\circ}C$$

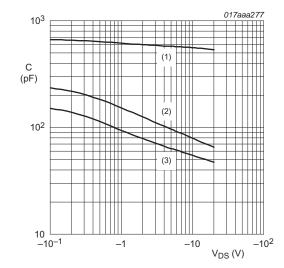
(2)  $T_i = 150 \, ^{\circ}\text{C}$ 

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$ 

Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



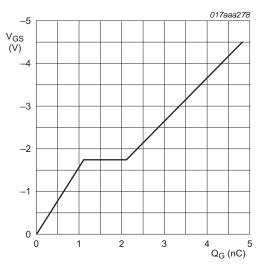
 $f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$ 

(1) C<sub>iss</sub>

(2) C<sub>oss</sub>

(3) C<sub>rss</sub>

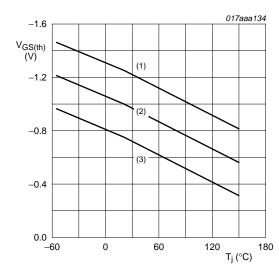
Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $I_D = -3 \text{ A}; V_{DS} = -10 \text{ V}; T_{amb} = 25 \text{ °C}$ 

Fig 13. Gate-source voltage as a function of gate charge; typical values

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 $I_D$  = -0.25 mA;  $V_{DS}$  =  $V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 14. Gate-source threshold voltage as a function of junction temperature

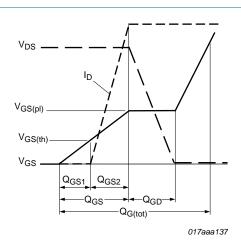
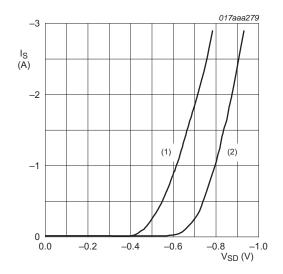


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$ 

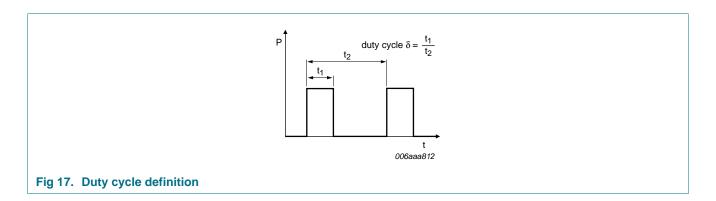
(1) T<sub>i</sub> = 150 °C

(2)  $T_j = 25 \, ^{\circ}C$ 

Fig 16. Source current as a function of source-drain voltage; typical values

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## 8. Test information



## Package outline

#### Plastic surface-mounted package; 6 leads **SOT363** Α X = v M A ⊕ w M B е detail X **DIMENSIONS** (mm are the original dimensions) Α1 UNIT D Ε Α С Q е HΕ Lp ٧ w у max 0.30 0.25 1.35 0.45 0.25 1.1 2.2 2.2 0.65 0.1 1.8 2.0 0.20 0.10 8.0 1.15 0.15 0.15 **REFERENCES EUROPEAN** OUTLINE ISSUE DATE VERSION **PROJECTION** JEDEC IEC **JEITA** 04-11-08 SOT363 SC-88

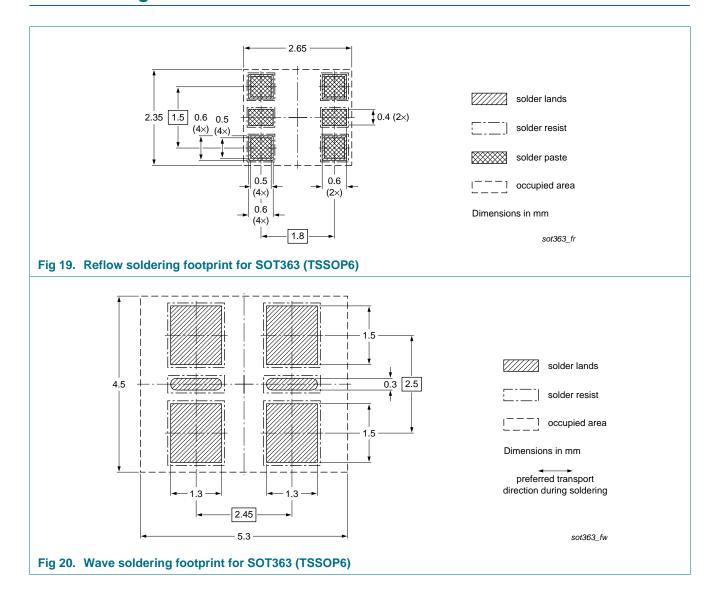
Fig 18. Package outline SOT363 (TSSOP6)

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06-03-16

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## 10. Soldering



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## 11. Revision history

#### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMG85XP v.N	20110628	Product data sheet	-	-

#### 20 V, 2 A P-channel Trench MOSFET

### 12. Legal information

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Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Product data sheet

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